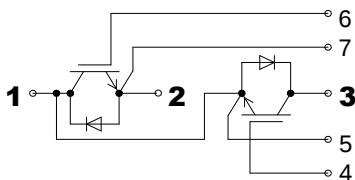


SGG300T170UC2

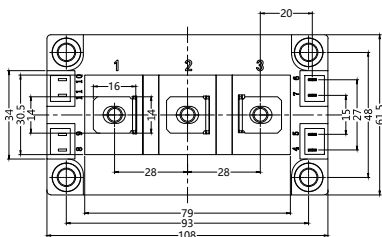
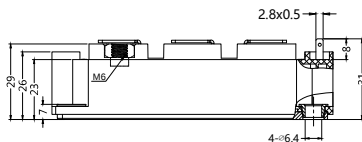
IGBT Modules



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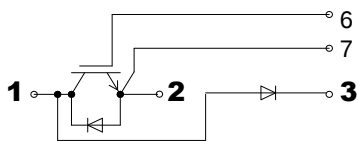


Dimensions in mm (1mm = 0.0394")

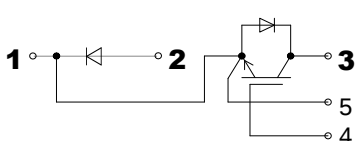


T_C = 25°C, unless otherwise specified

SGD300T170UC2



SDG300T170UC2



Symbol	Conditions	Values	Units
IGBT			
V _{CES}		1700	V
I _C	T _C = 25(100)°C	600(300)	A
I _{CRM}	T _C =25°C, t _p =1ms	600	A
V _{GES}		±20	V
T _{Vj}		-40...+175	°C
Inverse Diode			
V _{RRM}	T _C = 25(80)°C	1700	V
I _F =I _C		600(300)	A
I _{FRM}	T _C =25°C, t _p =1ms	600	A
I _{FSM}	t _p =10ms; sin.; T _j =150°C	600	A
Module			
I _{t(RMS)}	T _{terminal} =80°C	300	A
T _{stg}		-40~125	°C
V _{Isol}	AC, 1min	4000	V

Features

- Trench FS technology
- Low switching losses
- Square RBSOA, no latch up
- High short circuit capability
- Positive temperature coefficient for easy paralleling
- Soft switching FWD Technology
- Package with copper base plate
- Isolation voltage 4000V

Application

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters



Advantages

- space and weight savings
- reduced protection circuits

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SGG300T170UC2

IGBT Modules

Characteristics

$T_c = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_c=12\text{mA}$	5.0	5.5	6.2	V
I_{CES}	$V_{GE}=0; V_{CE}=V_{CES}; T_j=25^\circ\text{C}$			2.0	mA
$V_{CE(TO)}$	$T_j=25^\circ\text{C}$		0.86	0.96	V
r_{CE}	$V_{GE}=15\text{V}, T_j=25(150)^\circ\text{C}$		7.0(10.1)	7.9(10.7)	m Ω
$V_{CE(sat)}$	$I_c=300\text{A}; V_{GE}=15\text{V}; \text{chip level}$		2.05	2.50	V
C_{ies}	under following conditions $V_{GE}=0, V_{CE}=25\text{V}, f=1\text{MHz}$		21.0		nF
C_{oes}			1.19		
C_{res}			0.86		
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c=25(125)^\circ\text{C}$		0.26(0.6)		m Ω
$t_{d(on)}$	under following conditions: $V_{CC}=900\text{V}, I_c=300\text{A}$ $R_{Gon}=R_{Goff}=1\Omega, T_j=150^\circ\text{C}$ $V_{GE}=\pm 15\text{V}$		295		ns
t_r			72		ns
$t_{d(off)}$			500		ns
t_f			380		ns
$E_{on}(E_{off})$			54.7(58.1)		mJ
Inverse Diode					
V_{RRM}	under following conditions: $I_F=300\text{A}; V_{GE}=0\text{V}; T_j=25^\circ\text{C}$	1700			V
$V_F = V_{EC}$			2.98	3.50	V
$V_{(FO)}$	$T_j=25(150)^\circ\text{C}$		1.4(1.15)	1.8(1.45)	V
r_F	$T_j=25(150)^\circ\text{C}$		6.0(8.4)	6.6(9.0)	m Ω
I_{RRM}	$I_F=300\text{A}; T_j=150^\circ\text{C}$		170		A
Q_{rr}	$di/dt=3100\text{A}/\mu\text{s}$		79		μC
E_{rr}	$V_{GE}=\pm 15\text{V}$		52		mJ
Thermal Characteristics					
$R_{th(j-c)}$	per IGBT			0.070	K/W
$R_{th(j-c)D}$	per Inverse Diode			0.130	K/W
$R_{th(c-s)}$	per module			0.022	K/W
Mechanical Data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6	2.5		5	Nm
Weight	typical			320	g

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IGBT Modules

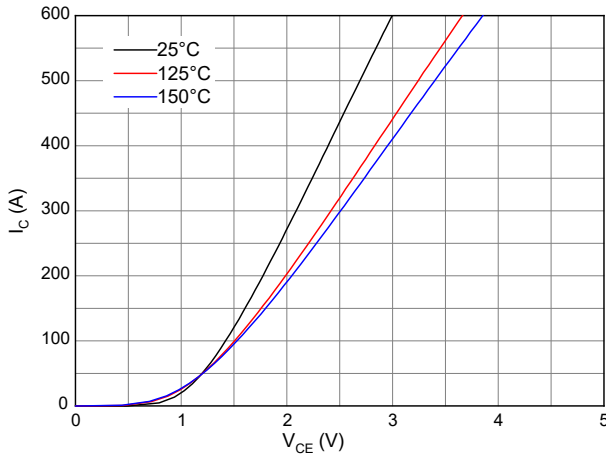


Figure 1. Typical output characteristics ($V_{GE}=15V$)

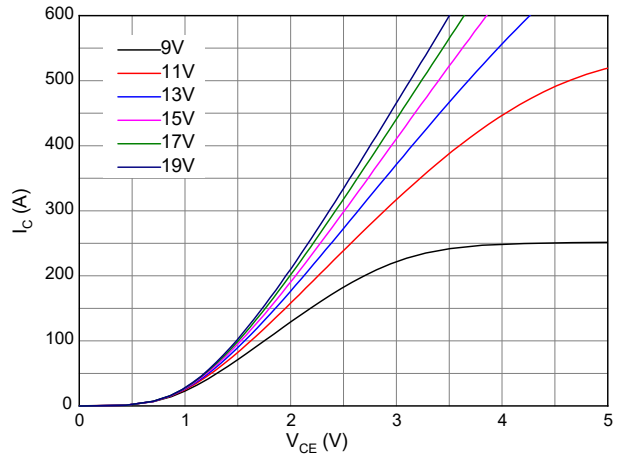


Figure 2. Typical output characteristics ($T_{vj}=150^{\circ}C$)

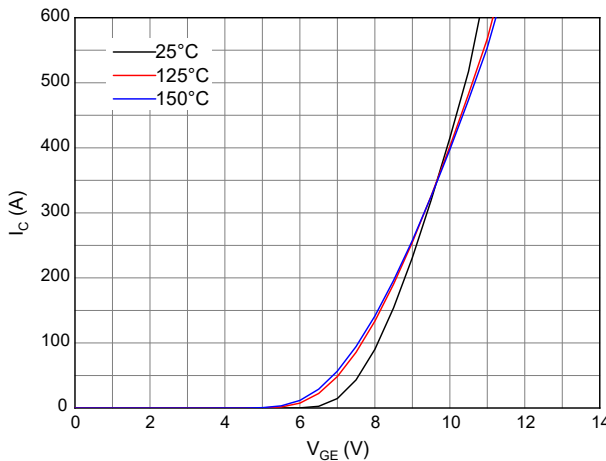


Figure 3. Typical transfer characteristic ($V_{CE}=20V$)

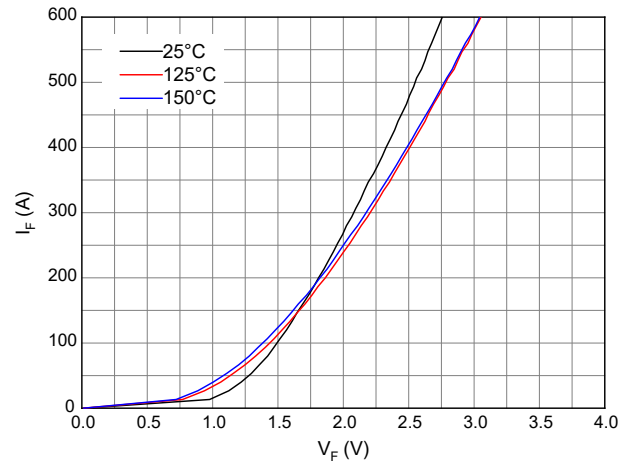


Figure 4. Forward characteristic of Diode

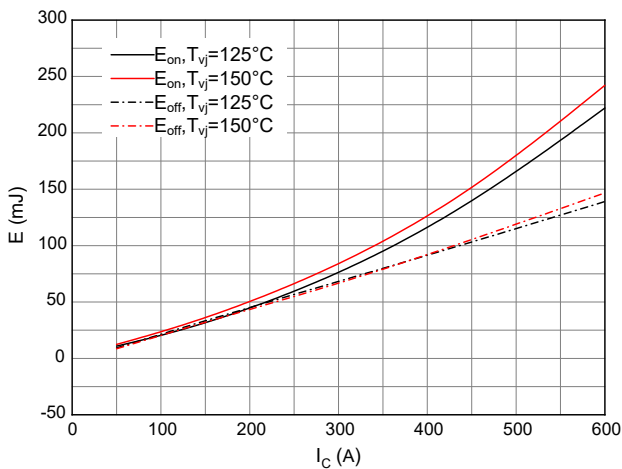


Figure 5. Switching losses of IGBT

$V_{GE}=\pm 15V$, $R_{Gon}=2.5\Omega$, $R_{Goff}=2.5\Omega$, $V_{CE}=900V$

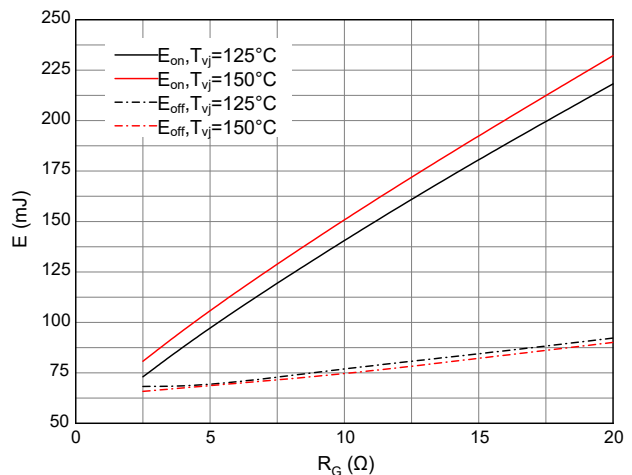


Figure 6. Switching losses of IGBT

$V_{GE}=\pm 15V$, $I_C=300A$, $V_{CE}=900V$

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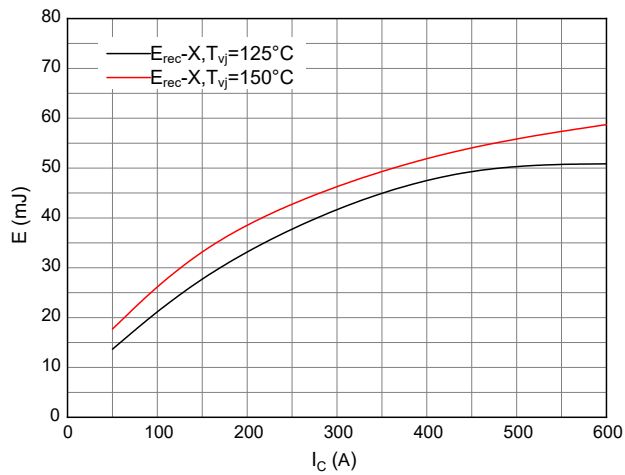


Figure 7. Switching losses of Diode

$R_{Gon}=2.5\Omega$, $V_{CE}=900V$

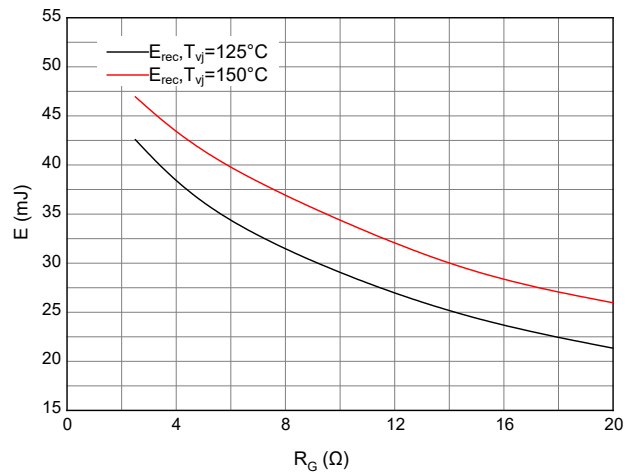


Figure 8. Switching losses of Diode

$I_F=300A$, $V_{CE}=900V$

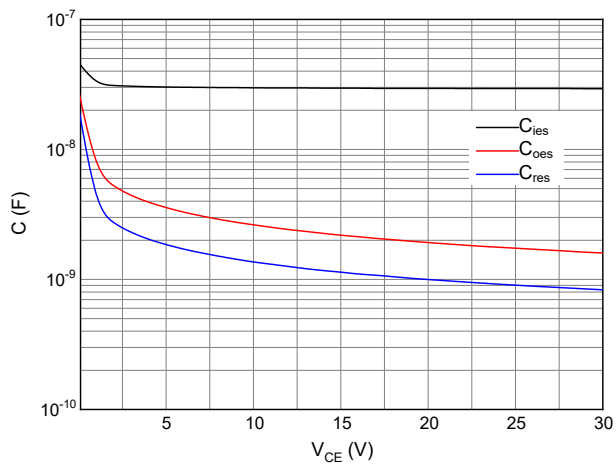


Figure 9. Capacitance characteristic